

ABSTRACT

The present invention relates to an electro-static chuck with non-sintered AlN and a method of preparing the same. Especially, the present
5 invention relates to the electro-static chuck with non-sintered AlN which having coated aluminum nitride (AlN) layer as a dielectric one on the purpose of chucking the wafers in the process of wafers and a method of preparing the same.

10 The electro-static chuck of the present invention has excellent dielectric characteristics, bonding strength and thermal conductivity by forming an AlN layer as a dielectric one without sintering process or bonding process with binders.